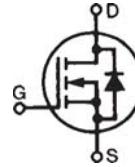


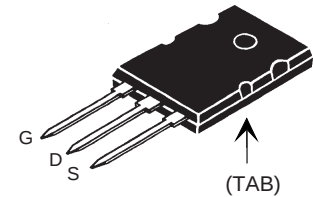
Linear Power MOSFET IXTK46N50L With Extended FBSOA IXTX46N50L

N-Channel Enhancement Mode

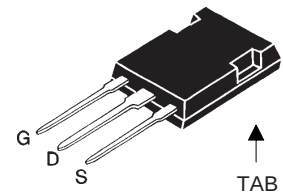


$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 46 \text{ A} \\ R_{DS(on)} &\leq 0.16 \text{ } \Omega \end{aligned}$$

TO-264 (IXTK)



PLUS247 (IXTX)


G = Gate
S = Source

D = Drain
TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	46	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	100	A
I_{AR}	$T_C = 25^\circ\text{C}$	46	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ
E_{AS}		1.5	J
P_D	$T_C = 25^\circ\text{C}$	700	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-264)	1.13/10	Nm/lb.in.
F_c	Mounting force (PLUS247™)	20...120/4.5...27	N/lb.
Weight	PLUS247	6	g
	TO-264	10	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ } \mu\text{A}$	3		6 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $T_J = 25^\circ\text{C}$			50 μA
	$V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			1 mA
$R_{DS(on)}$	$V_{GS} = 20 \text{ V}$, $I_D = 0.5 I_{D25}$, Note 1			0.16 Ω

Features

- Designed for linear operation
- International standard package
- Unclamped Inductive switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Programmable loads
- Current regulators
- DC-DC converters
- Battery chargers
- DC choppers
- Temperature and lighting controls

Advantages

- Easy to mount
- Space savings
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)			
		Min.	Typ.	Max.	
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = 0.5 \cdot I_{D25}$, Note 1	7	10	13	S
C_{iss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		7000		pF
C_{oss}			900		pF
C_{rss}			170		pF
$t_{d(on)}$	$V_{GS} = 15 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2 \Omega$ (External),		40		ns
t_r			50		ns
$t_{d(off)}$			80		ns
t_f			42		ns
$Q_{g(on)}$	$V_{GS} = 15 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		260		nC
Q_{gs}			85		nC
Q_{gd}			125		nC
R_{thJC}			0.15	0.18	°C/W
R_{thCS}					°C/W

Safe Operating Area Specification

Symbol	Test Conditions	Min.	Typ.	Max.
SOA	$V_{DS} = 400 \text{ V}, I_D = 0.6 \text{ A}, T_C = 90^\circ\text{C}$	240		W

Source-Drain Diode

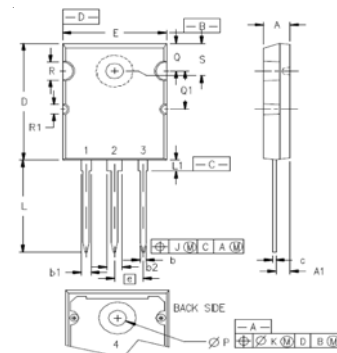
Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0 \text{ V}$			46 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			100 A
V_{SD}	$I_F = I_S, V_{GS} = 0 \text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100\text{V}$		600	ns

Note 1: Pulse test, t < 300 μs, duty cycle, d ≤ 2 %

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

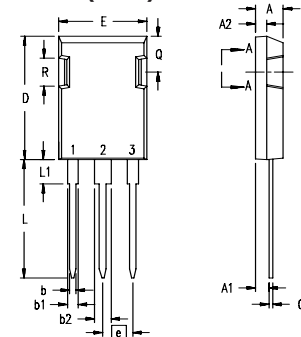
TO-264 (IXTK) Outline



- 1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247™ (IXTX) Outline



- Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

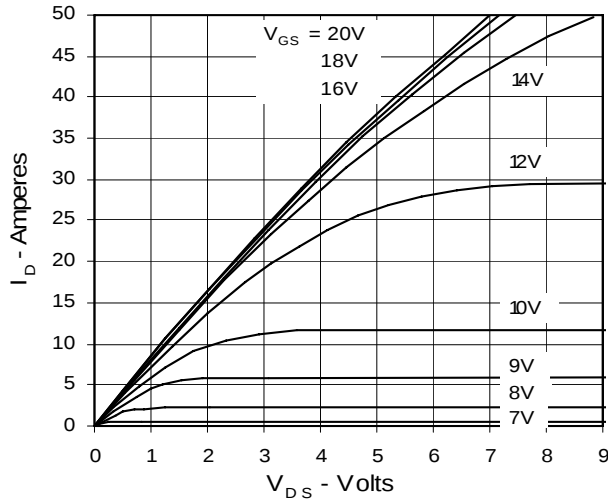


Fig. 2. Extended Output Characteristics
@ 25°C

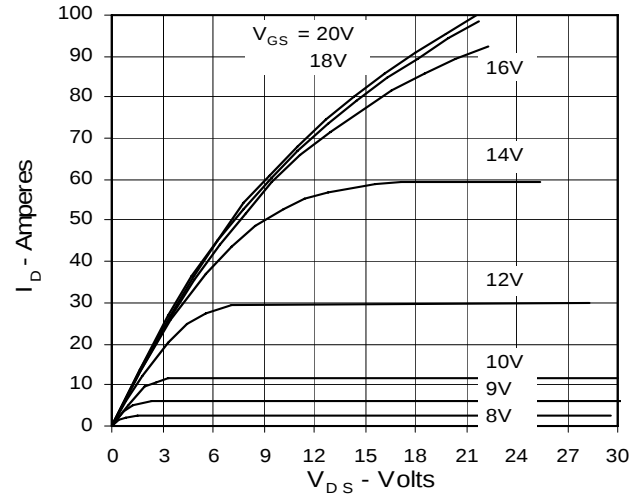


Fig. 3. Output Characteristics
@ 125°C

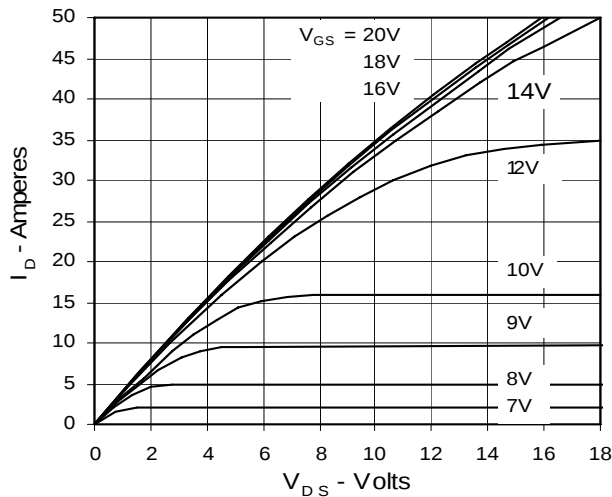


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. Junction Temperature

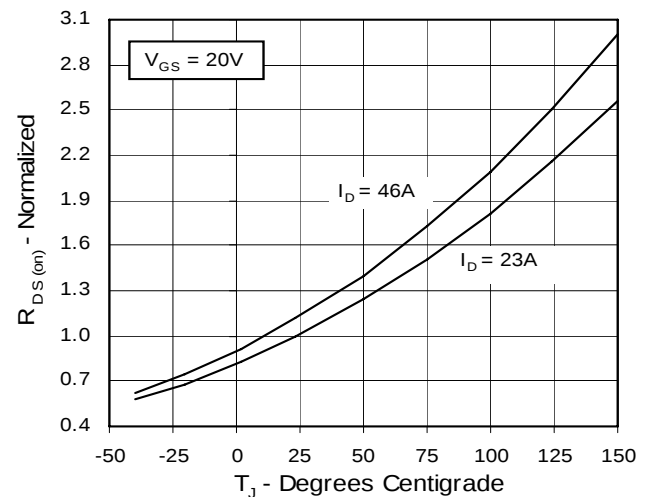


Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D

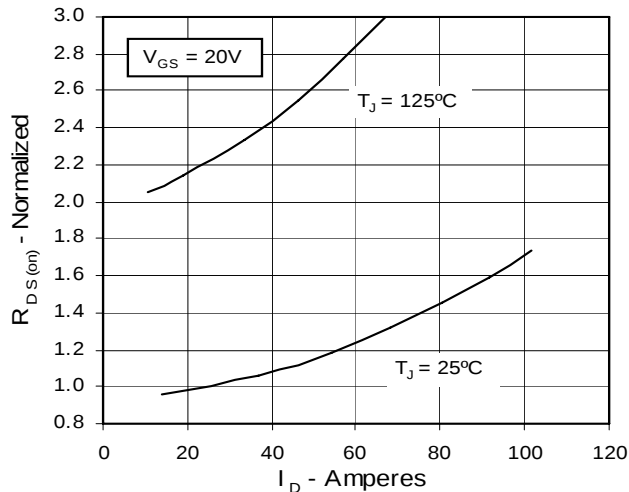


Fig. 6. Drain Current vs. Case
Temperature

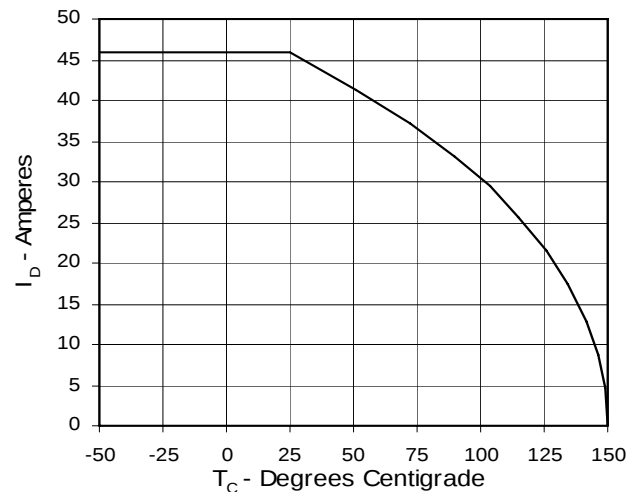


Fig. 7. Input Admittance

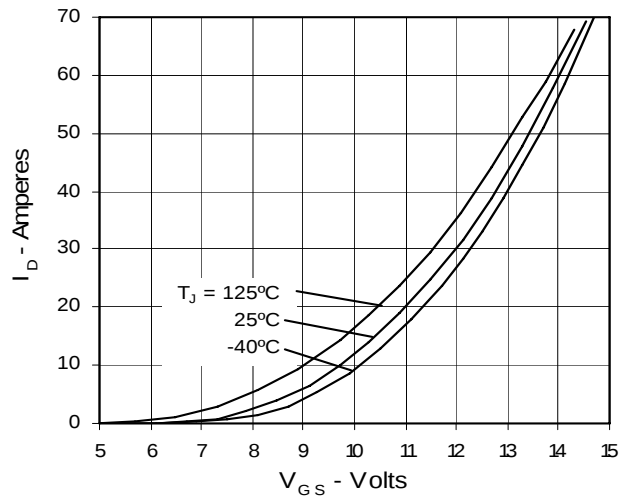


Fig. 8. Transconductance

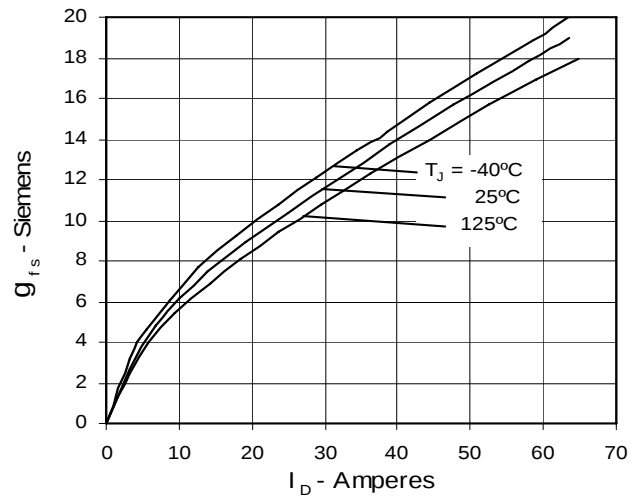


Fig. 9. Source Current vs. Source-To-Drain Voltage

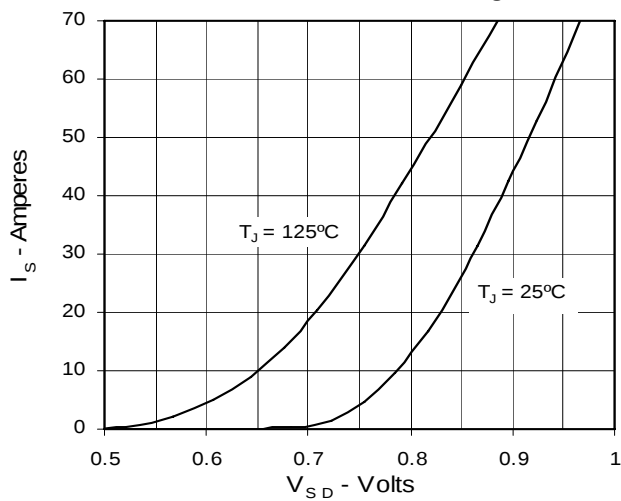


Fig. 10. Gate Charge

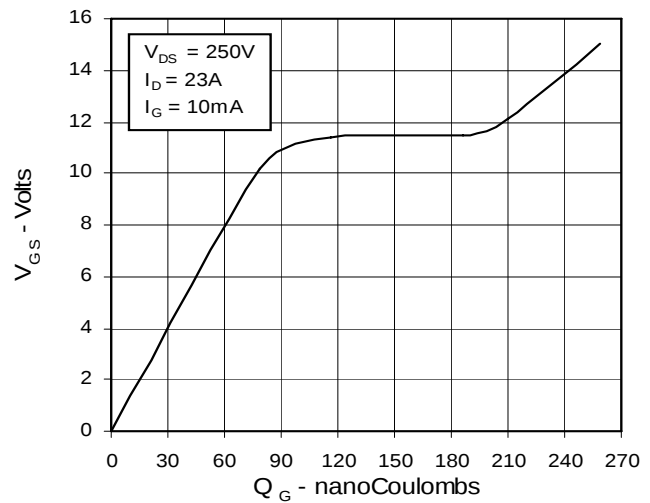
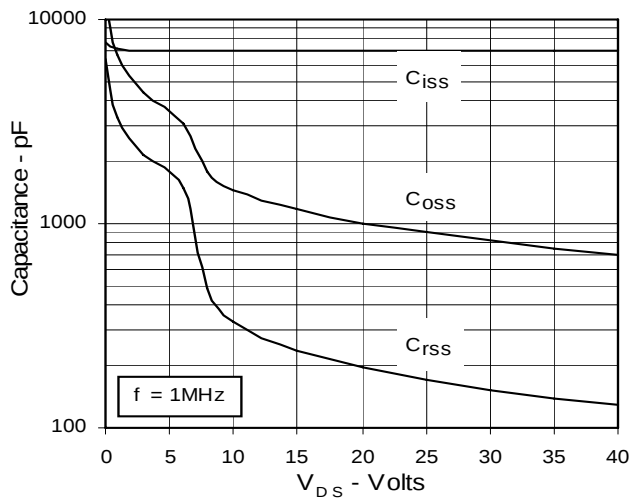
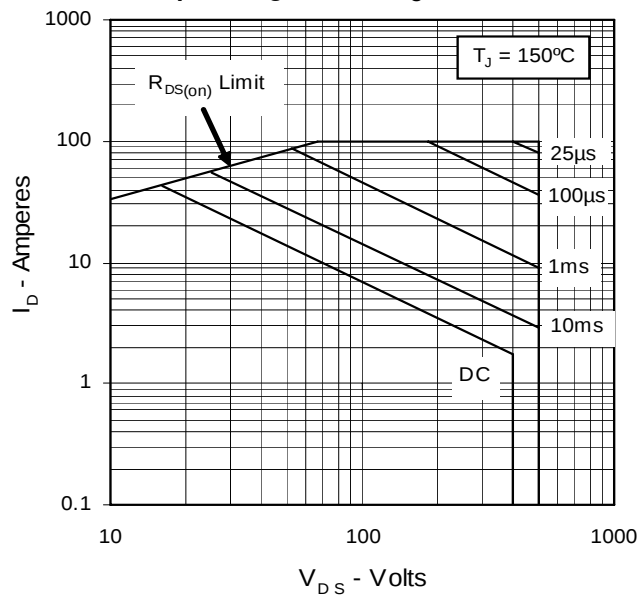


Fig. 11. Capacitance



**Fig. 12. Forward-Bias Safe
Operating Area @ $T_C = 25^\circ\text{C}$**



**Fig. 13. Forward-Bias Safe
Operating Area @ $T_C = 90^\circ\text{C}$**

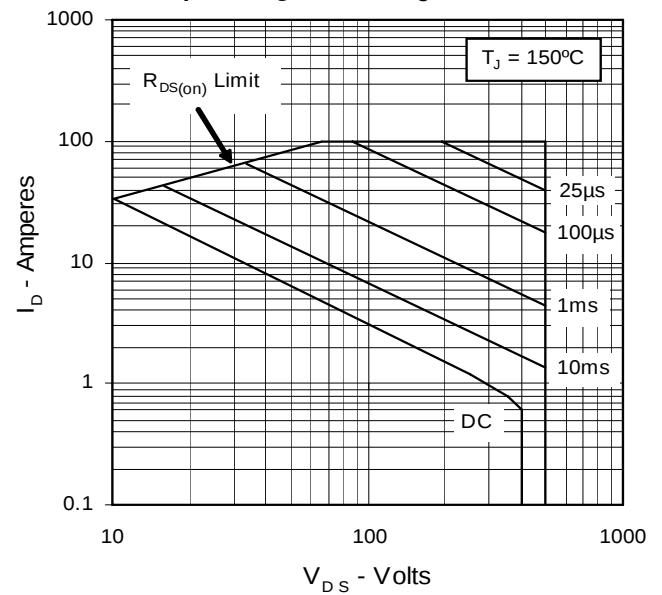


Fig. 14. Maximum Transient Thermal Impedance

